

2N174 Transistors

Ge PNP Power BJT

Military/High-Rel N

$V_{(BR)CEO}$ (V) 70

$V_{(BR)CBO}$ (V) 80

I_C Max. (A) 15

Absolute Max. Power Diss. (W) 30

Maximum Operating Temp ($^{\circ}C$) 95

I_{CBO} Max. (A) 8.0m

@ $V_{(CBO)}$ (V) (Test Condition) 80

$V_{(CE)sat}$ Max. (V) 0.9

@ I_C (A) (Test Condition) 12

@ I_B (A) (Test Condition) 2.0

$h_{(FE)}$ Min. Current gain. 25

$h_{(FE)}$ Max. Current gain. 50

@ I_C (A) (Test Condition) 5.0

@ $V_{(CE)}$ (V) (Test Condition) 2.0

f_T Min. (Hz) Transition Freq 10k

@ I_C (A) (Test Condition) 5.0

@ $V_{(CE)}$ (V) (Test Condition) 6.0

t_r Max. (s) Rise time 15 μ s

t_f Max. (s) Fall time. 15 μ s

Package Style TO-36